

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re DIVISIONAL application of )  
Shunpei YAMAZAKI et al. )  
Based on Serial No. 10/214,691 ) Group Art Unit: 2826  
Filed: August 9, 2002 ) Examiner: Abraham  
For: SEMICONDUCTOR DEVICE AND )  
METHOD OF FABRICATING SAME )

INFORMATION DISCLOSURE STATEMENT

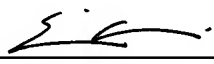
Commissioner for Patents  
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Alexandria, Virginia 22313-1450

Sir:

In accordance with the provisions of 37 C.F.R. 1.56 and 37 C.F.R. 1.97-1.99, Applicant submits herewith a Form PTO-1449 listing references known to Applicant and requests that these references be made of record in the above identified application. Copies of the references listed are submitted herewith in accordance with 37 C.F.R. 1.98(a).

The references listed on the attached Form PTO-1449 were cited in parent application Serial No. 10/214,691 and predecessor Application Serial No. 08/785,486 and copies of the references can be found in those applications.

Respectfully submitted,

  
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Substitute for form 1449A/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(use as many sheets as necessary)</i>				<b>Complete if Known</b>	
				Application Number	Based on 10/214,691
				Filing Date	August 9, 2002
				First Named Inventor	Shunpei YAMAZAKI, et al.
				Group Art Unit	2826
Examiner Name	Fetsum Abraham				
Sheet	1	of	12	Attorney Docket Number	0756-7218

U.S. PATENT DOCUMENTS						
Examiner Initials <sup>*</sup>	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			
		5,686,328		Zhang et al.	11/11/97	
		5,763,899		Yamazaki et al.	06/09/98	
		5,782,665		Weisfield et al.	07/21/98	
		5,922,125		Zhang	07/13/99	
		6,083,801		Ohtani	07/04/00	
		5,744,822		Takayama et al.	04/28/98	
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		5,766,977		Yamazaki	06/16/98	
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		5,949,107		Zhang	09/07/99	
		6,031,249		Yamazaki et al.	02/29/00	
		6,121,683		Yamazaki et al.	09/19/00	
		6,207,969 B1		Yamazaki et al.	03/27/01	

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials <sup>*</sup>	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
		Japan J. Appl. Phys. 8 (1969) 1056, "Effect of Deposited Metals on the Crystallization Temperature of Amorphous Germanium Film," OKI et al.	
		Technology Information Association, "Thermo-Auto-Chrome Full Color Recording Technology," May 31, 1995	

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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup> Unique citation designation number. <sup>2</sup> See attached Kinds of U.S. Patent Documents. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

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		5,811,327		Funai et al.	09/22/98	
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		4,544,418		Gibbons	10/01/85	

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		Office <sup>3</sup>	Number <sup>4</sup> Kind Code <sup>2</sup> (if known)			
		JP	07-335900	Teramoto Satoshi	12/22/95	Abst.
		JP	64-081324		03/27/89	Abst.

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
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		IBM Technical Disclosure Bulletin, Vol. 11, No.7, A.R. Baker, Jr.	

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		4,546,376		Nakata et al.	10/08/85	
		4,597,160		Ipri	07/01/86	
		4,634,473		Swartz et al.	01/06/87	
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		Number	Kind Code <sup>2</sup> (if known)			
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		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)				
		EP	0 178 447			10/09/84		English
		JP	01-187814			07/27/89		Full
		JP	01-187874			07/27/89		Abst.
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		JP	03-280420			12/11/91		Full
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		JP	05-299348			11/12/93		Abst.
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		JP	61-063017			04/01/86		Full
		JP	61-063107			04/01/86		Abst.
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		Caune et al., "Combined CW Laser and Furnace Annealing of Amorphous Si and Ge in Contact With Some Metals," January 1, 1989, pp. 597-604, Applied Surface Science, Vol. 36	
		Stoemnos et al., "Crystallization of Amorphous Silicon by Reconstructive Transformation Utilizing Gold," March 18, 1991, pp. 1196-1198, Appl. Phys. Lett. 58(11)	
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		Green et al., "Method to Purify Semiconductor Wafers," October 1973, pp. 1612-1613, IBM Tech. Discl. Bulletin, Vol. 16, No. 5	
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		Wolf et al., "Silicon Processing for the VLSI Era Volume 1: Process Technology," 1986, pp. 215-216, Lattice Press	

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		Lau et al., "Solid Phase Epitaxy in Silicide Forming System," 1977, pp. 313-322, Thin Solid Films, 47	
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				First Named Inventor	
		Shunpei YAMAZAKI, et al.			
Group Art Unit		2826			
Examiner Name		Fetsum Abraham			
Sheet	8	of	12	Attorney Docket Number	0756-7218

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		Number	Kind Code <sup>2</sup> (if known)			
		5,705,829		Miyanaga et al.	01/06/98	
		5,712,191		Nakajima et al.	01/27/98	
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		5,693,959		Inoue et al.	12/02/97	

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		5,426,064		Zhang et al.	06/20/95	
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		4,759,610		Yanagisawa	07/26/88	
		5,535,471		Guldi	07/16/96	
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		Wolf, <i>Silicon Processing for the VLSI Era</i> , Volume 2, Chapter 4, page 274 (1990).	

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		6,225,152	B1	Yamazaki et al.	05/01/01	
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		6,331,718	B1	Yamazaki et al.	12/18/01	

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